

iADC3_4

iADC: Experimental Sub-Ranging Current-Mode Current I_{IN} Asynchronous Ultra-Low-Power iADC

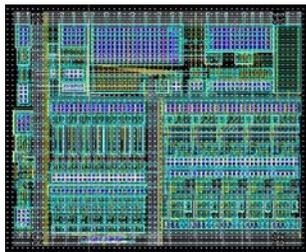
Proof of silicon: 4Q24 | IC testing in progress | Simulation results below

Please contact sales@ailinear.com for more information & ordering specific evaluation.

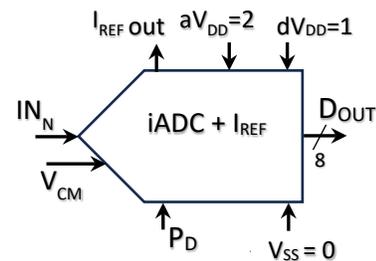
Parameter (units)	Typical Simulation Spec	Typical Conditions: $V_{DD}=2V$, Temperature = 27C, unless otherwise stated
Resolution (Bits)	8	
I_{IN} peak-to-peak (nA)	$0 \rightarrow I_{REF}$	$I_{REF} \approx 256nA$
V_{CM} (v)	$0.5 \times aV_{DD}$	I_{IN} current source compliance voltage (rails $\pm V_{GS}$)
I_{REF} Output (nA)	25.6	
a V_{DD} High (v)	~ 2	
a V_{DD} Low (v)	~ 1	a V_{DD} sweep $0v \rightarrow 2v$
I_{DD} (nA)	~ 885	$I_{IN} \approx$ full-scale. $I_{REF} \approx 256nA$
Integral Non-Linearity = INL (LSB)	$\sim \pm 1.5$	I_{IN} sweep $0 \rightarrow$ Full-Scale
Gain Error (LSB)	$\sim \pm 10$	I_{IN} sweep $0 \rightarrow$ Full-Scale
Input Bandwidth = A_{INBW} (KHz)	tbd	-3dB frequency
Transient Time = τ (μs)	38	D_{OUT} time from I_{IN} pulse $\frac{1}{4}$ to $\frac{3}{4}$ scale in $1\mu s$
Digital I/O Levels (v)	$0 \rightarrow dV_{DD}$	
Cell Size ($\mu m \times \mu m$)	$\sim 290 \times 240$	
TSMC Process Node (nm)	180	

See Disclaimers

iADC + I_{REF} Cell Layout



iADC + I_{REF} Block Diagram



Features:

- Patented segmented sub-ranging iADC. Thermometer-based Most-Significant-Portion (MSP) of iADC's first stage reference network inherently enhances the accuracy of the overall iADC
- Optional: Programmable internal I_{REF} customizes I_{IN} peak-to-peak ranges, supporting range calibration via I_{REF} output.
- Optional: Digital output port (D_{OUT}) can be serialized as needed.
- Digital power consumption reduces dynamically in steady-state I_{IN} conditions, enabled by asynchronous iADC architecture.
- iADC includes power-down (P_D) and I_{IN} current source compliance (V_{CM}) voltage setting capabilities.